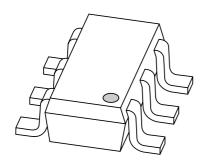
DISCRETE SEMICONDUCTORS

DATA SHEET



BC807DS PNP general purpose double transistor

Product data sheet Supersedes data of 2002 Aug 09 2002 Nov 22



PNP general purpose double transistor

BC807DS

FEATURES

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

APPLICATIONS

- · General purpose switching and amplification
- Push-pull amplifiers
- · Multi-phase stepper motor drivers.

DESCRIPTION

PNP transistor pair in a SOT457 (SC-74) plastic package.

MARKING

TYPE NUMBER	MARKING CODE	
BC807DS	N2	

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-45	V
I _C	collector current (DC)	-500	mA
I _{CM}	peak collector current	-1	Α

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	

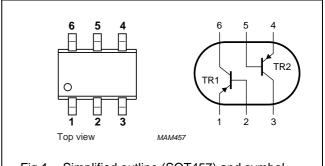


Fig.1 Simplified outline (SOT457) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	Per transistor unless otherwise specified				
V_{CBO}	collector-base voltage	open emitter	_	-50	V
V_{CEO}	collector-emitter voltage	open base	_	-45	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-500	mA
I _{CM}	peak collector current		_	-1	Α
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	370	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	•		·		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	600	mW

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	208	K/W
	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

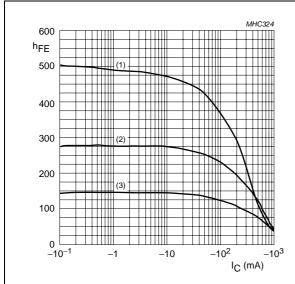
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor		•		•	•
I _{CBO}	collector-base cut-off current	$V_{CB} = -20 \text{ V}; I_E = 0$	_	_	-100	nA
		$V_{CB} = -20 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V; } I_{C} = -100 \text{ mA; note 1}$	160	_	400	
		$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA; note 1}$	40	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}$; $I_B = -50 \text{ mA}$; note 1	_	_	-700	mV
V_{BE}	base-emitter voltage	$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA;}$ notes 1 and 2	_	_	-1.2	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	9	_	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	80	_	_	MHz

Notes

- 1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$
- 2. V_{BE} decreases by approximately -2 mV/K with increasing temperature.

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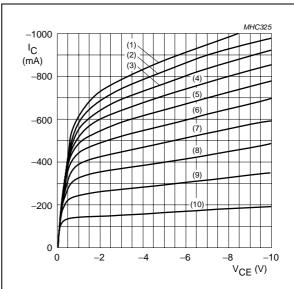
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 $V_{CE} = 1 V$.

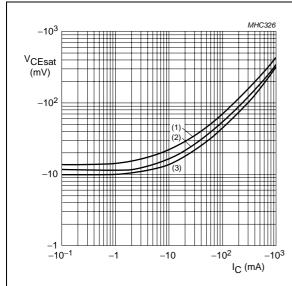
- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



- (1) $I_B = -7 \text{ mA}$.
- (5) $I_B = -4.2 \text{ mA}.$ (6) $I_B = -3.5 \text{ mA}.$
- (9) $I_B = -1.4 \text{ mA}.$ (10) $I_B = -0.7 \text{ mA}.$
- (2) $I_B = -6.3 \text{ mA}.$ (3) $I_B = -5.6 \text{ mA}.$
- (7) $I_B = -2.8 \text{ mA}.$
- (4) $I_B = -4.9 \text{ mA}$. (8)
- (8) $I_B = -2.1 \text{ mA}.$

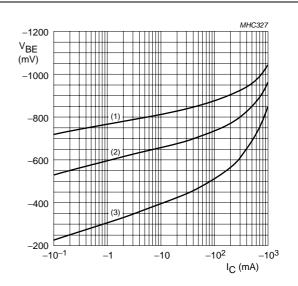
Fig.3 Collector current as a function of collector-emitter voltage; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = 1 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter voltage as a function of collector current; typical values.

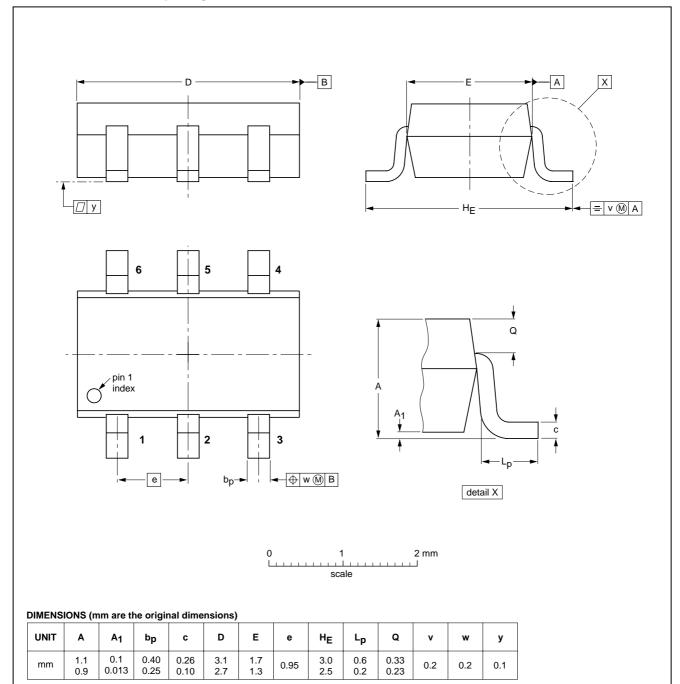
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATE	
SOT457			SC-74			97-02-28 01-05-04

PNP general purpose double transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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